Dual Enhancement Mode MOSFET (N and P-Channel)

Features

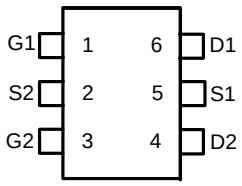
- N-Channel
  20V/3A,
  $R_{DS(ON)}$=50mΩ(typ.) @ V_{GS}=4.5V
  $R_{DS(ON)}$=90mΩ(typ.) @ V_{GS}=2.5V
- P-Channel
  -20V/-1.5A,
  $R_{DS(ON)}$=145mΩ(typ.) @ V_{GS}=-4.5V
  $R_{DS(ON)}$=180mΩ(typ.) @ V_{GS}=-2.5V
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free Available (RoHS Compliant)

Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems

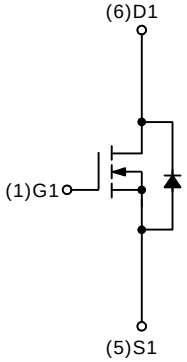
Pin Description

Top View

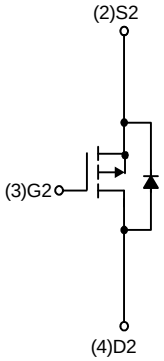


JSOT-6

Top View of JSOT-6



N-Channel MOSFET



P-Channel MOSFET

Ordering and Marking Information

APM2701 □□-□□ □ Lead Free Code Handling Code Temp. Range Package Code	Package Code CG : JSOT-6 Operating Junction Temp. Range C : -55 to 150 C Handling Code TR : Tape & Reel Lead Free Code L : Lead Free Device Blank : Original Device
APM2701CG : M71X	XXXXX - Date Code

Note: ANPEC lead-free products contain molding compounds/die attach materials and 100% matte in plate termination finish; which are fully compliant with RoHS and compatible with both SnPb and lead-free soldiering operations. ANPEC lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J STD-020C for MSL classification at lead-free peak reflow temperature.

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

Symbol	Parameter		N Channel	P Channel	Unit
V_{DSS}	Drain-Source Voltage		20	-20	V
V_{GSS}	Gate-Source Voltage		±10	±10	
I_D*	Continuous Drain Current	V_{GS}=±4.5V	3	-1.5	A
I_{DM}*	300µs Pulsed Drain Current		10	-6	
I_S*	Diode Continuous Forward Current		1	-1	A
T_J	Maximum Junction Temperature		150		°C
T_{STG}	Storage Temperature Range		-55 to 150		
P_D*	Power Dissipation	T_A=25°C	0.83		W
		T_A=100°C	0.3		
$R_{\theta JA}$*	Thermal Resistance-Junction to Ambient		150		°C/W

Note:

*Surface Mounted on 1in² pad area, t ≤ 10sec.

Electrical Characteristics (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition		APM2701CG			Unit
				Min.	Typ.	Max.	
Static Characteristics							
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250µA	N-Ch	20			V
		V_{GS}=0V, I_{DS}=-250µA	P-Ch	-20			
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=16V, V_{GS}=0V	N-Ch			1	µA
		T_J=85°C				30	
		V_{DS}=-16V, V_{GS}=0V	P-Ch			-1	
		T_J=85°C				-30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250µA	N-Ch	0.45	0.6	1	V
		V_{DS}=V_{GS}, I_{DS}=-250µA	P-Ch	-0.45	-0.6	-1	
I_{GSS}	Gate Leakage Current	V_{GS}=±10V, V_{DS}=0V	N-Ch			±100	nA
			P-Ch			±100	
$R_{DS(ON)}$ [a]	Drain-Source On-State Resistance	V_{GS}=4.5V, I_{DS}=3A	N-Ch		50	70	mΩ
		V_{GS}=-4.5V, I_{DS}=-1.5A	P-Ch		145	190	
		V_{GS}=2.5V, I_{DS}=1.7A	N-Ch		90	110	
		V_{GS}=-2.5V, I_{DS}=-1A	P-Ch		180	235	

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Electrical Characteristics (Cont.) (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition		APM2701CG			Unit
				Min.	Typ.	Max.	
Static Characteristics (Cont.)							
V_{SD} [a]	Diode Forward Voltage	I_{SD}=0.5A, V_{GS}=0V	N-Ch		0.7	1.3	V
		I_{SD}=-0.5A, V_{GS}=0V	P-Ch		-0.7	-1.3	
Dynamic Characteristics [b]							
C_{iss}	Input Capacitance	N-Channel V_{GS}=0V, V_{DS}=10V, Frequency=1.0MHz P-Channel V_{GS}=0V, V_{DS}=-10V, Frequency=1.0MHz	N-Ch		270		pF
			P-Ch		300		
C_{oss}	Output Capacitance		N-Ch		70		
			P-Ch		50		
C_{rss}	Reverse Transfer Capacitance		N-Ch		50		
			P-Ch		30		
$t_{d(ON)}$	Turn-on Delay Time	N-Channel V_{DD}=10V, R_L=10Ω, I_{DS}=1A, V_{GEN}=4.5V, R_G=6Ω P-Channel V_{DD}=-10V, R_L=10Ω, I_{DS}=-1A, V_{GEN}=-4.5V, R_G=6Ω	N-Ch		6	12	ns
			P-Ch		6	10	
T_r	Turn-on Rise Time		N-Ch		5	10	
			P-Ch		8	12	
$t_{d(OFF)}$	Turn-off Delay Time		N-Ch		12	23	
			P-Ch		10	15	
T_f	Turn-off Fall Time		N-Ch		6	12	
			P-Ch		5	10	
Gate Charge Characteristics [b]							
Q_g	Total Gate Charge	N-Channel V_{DS}=10V, V_{GS}=4.5V, I_{DS}=3A P-Channel V_{DS}=-10V, V_{GS}=-4.5V, I_{DS}=-1.5A	N-Ch		5	6.5	nC
			P-Ch		4	6	
Q_{gs}	Gate-Source Charge		N-Ch		0.5		
			P-Ch		0.6		
Q_{gd}	Gate-Drain Charge		N-Ch		1.6		
			P-Ch		1		

Notes:

a : Pulse test ; pulse width ≤300μs, duty cycle ≤ 2%.

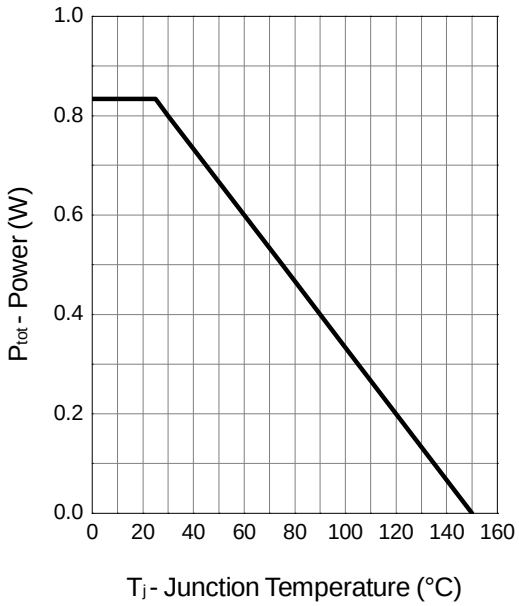
b : Guaranteed by design, not subject to production testing.

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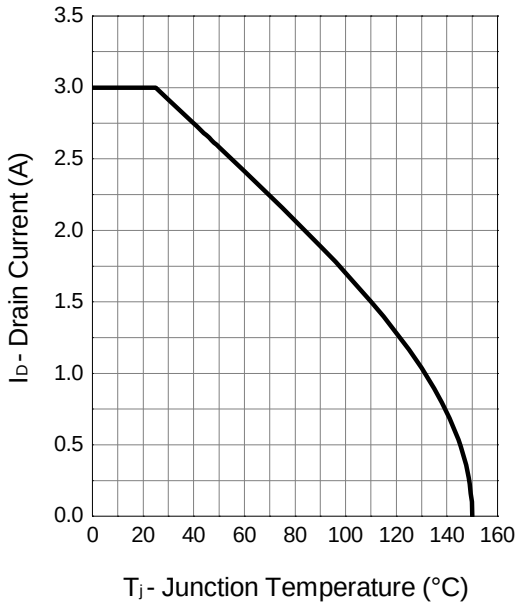
Typical Characteristics

N-Channel

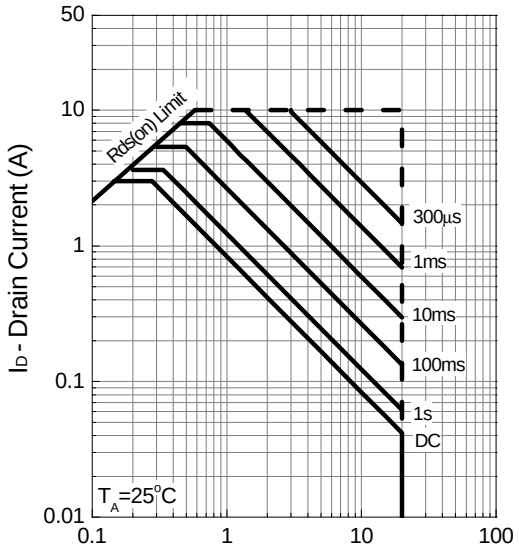
Power Dissipation



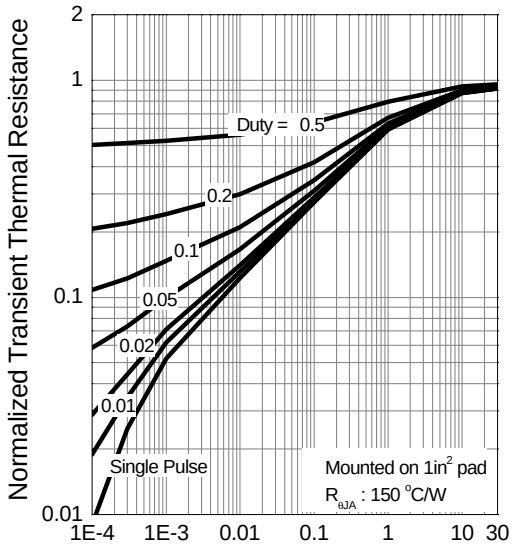
Drain Current



Safe Operation Area



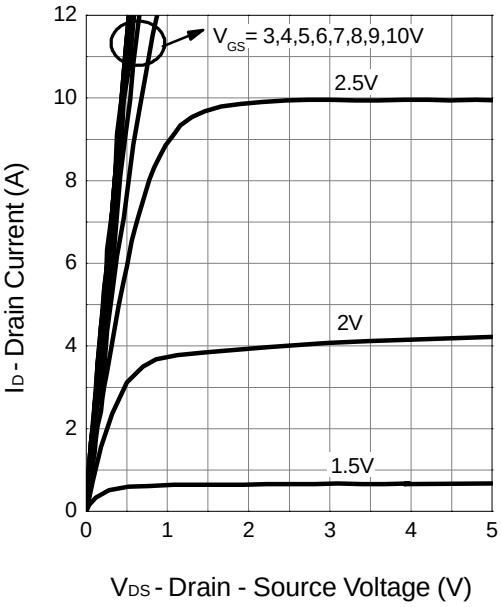
Thermal Transient Impedance



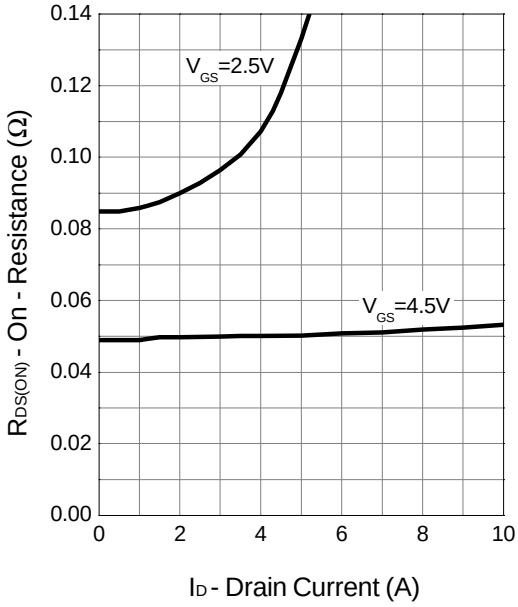
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Typical Characteristics (Cont.)

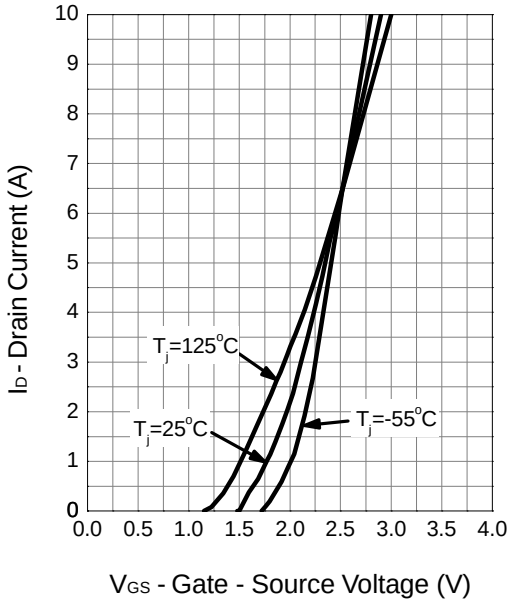
Output Characteristics



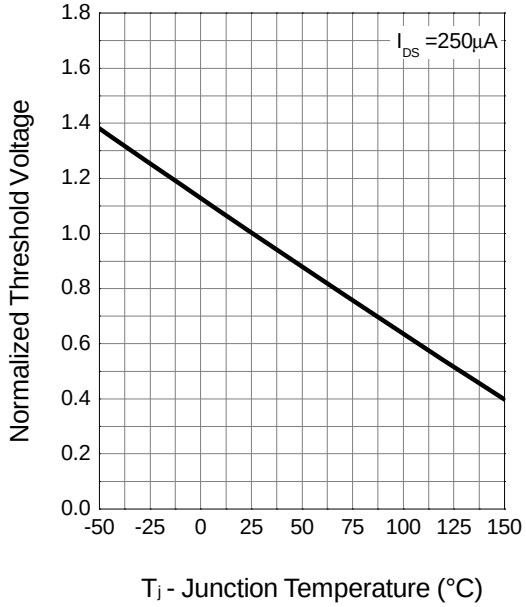
Drain-Source On Resistance



Transfer Characteristics



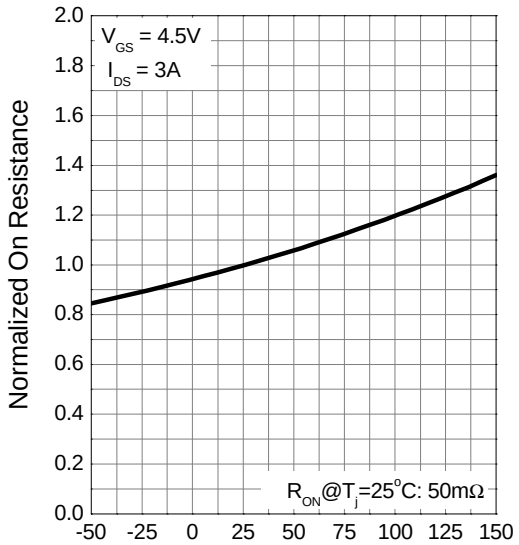
Gate Threshold Voltage



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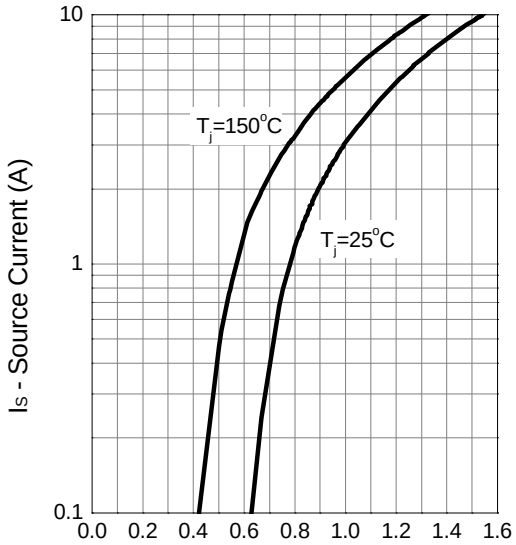
Typical Characteristics (Cont.)

Drain-Source On Resistance



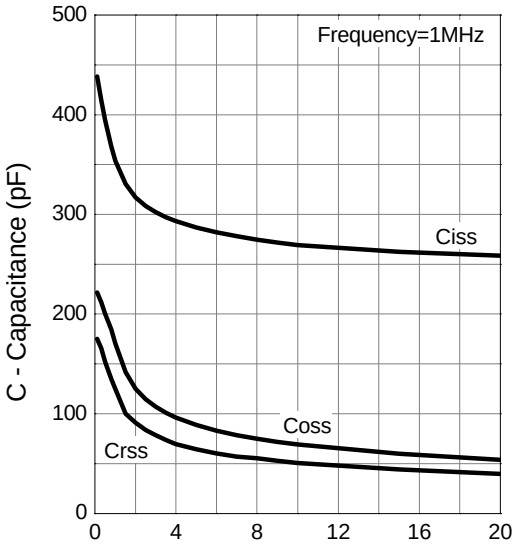
T_j - Junction Temperature (°C)

Source-Drain Diode Forward



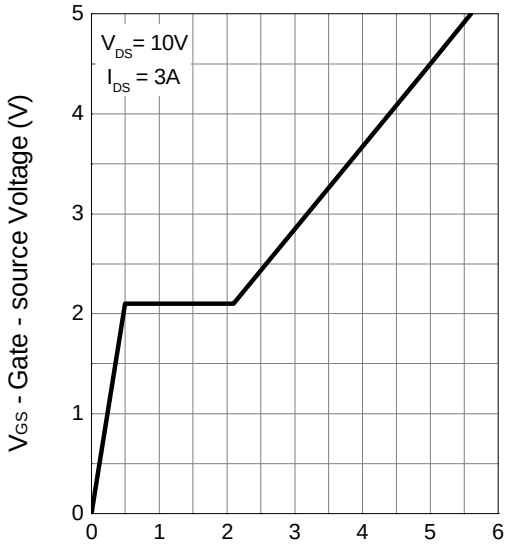
V_{SD} - Source - Drain Voltage (V)

Capacitance



V_{DS} - Drain - Source Voltage (V)

Gate Charge



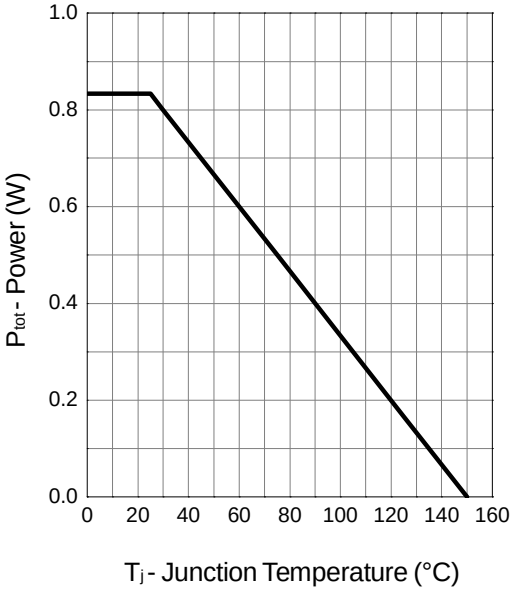
Q_G - Gate Charge (nC)

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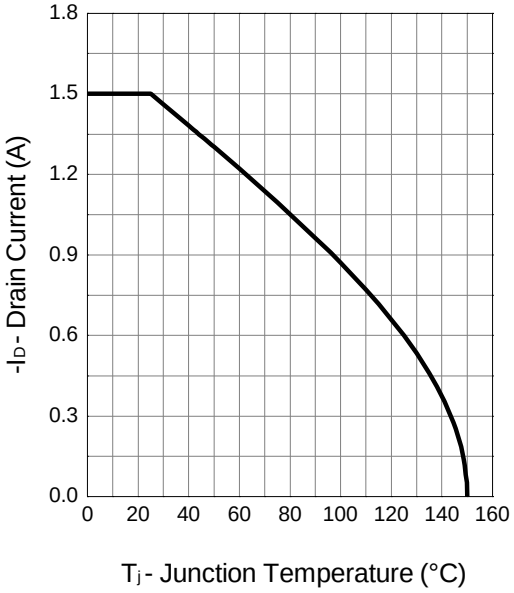
Typical Characteristics

P-Channel

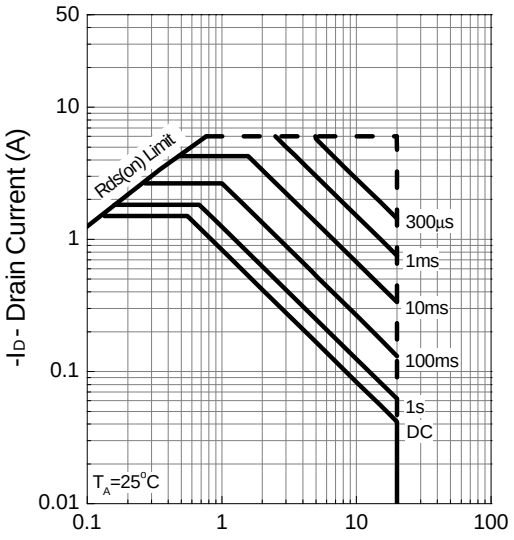
Power Dissipation



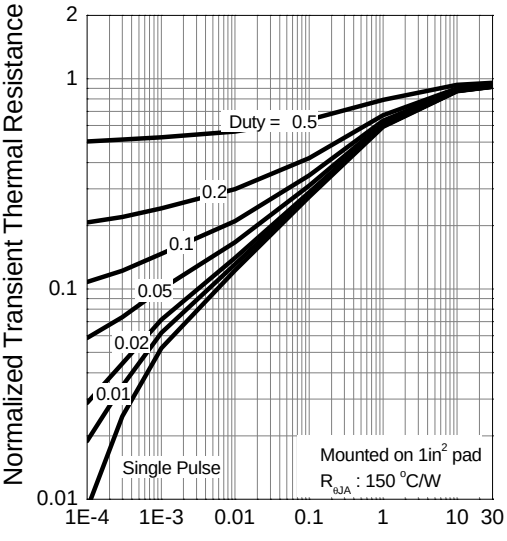
Drain Current



Safe Operation Area

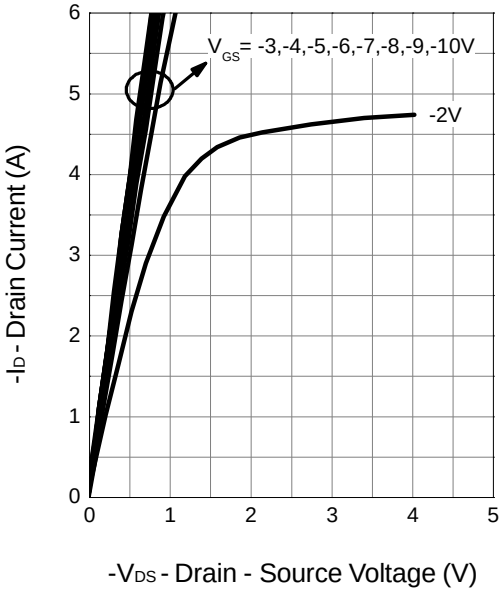


Thermal Transient Impedance

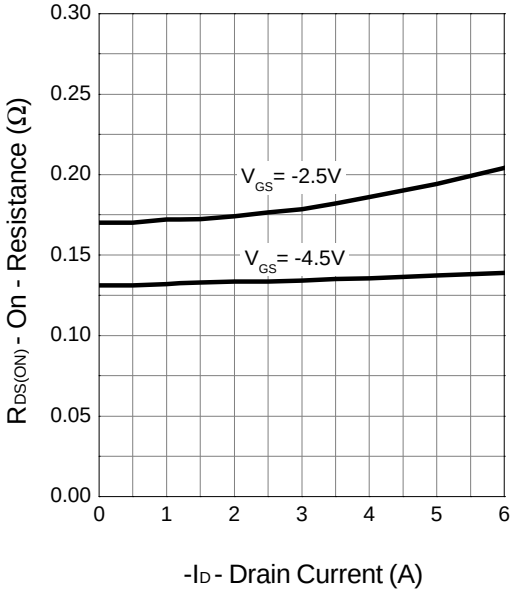


Typical Characteristics (Cont.)

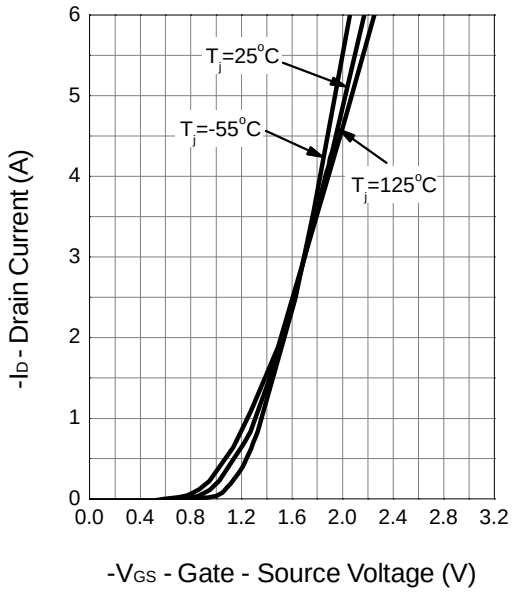
Output Characteristics



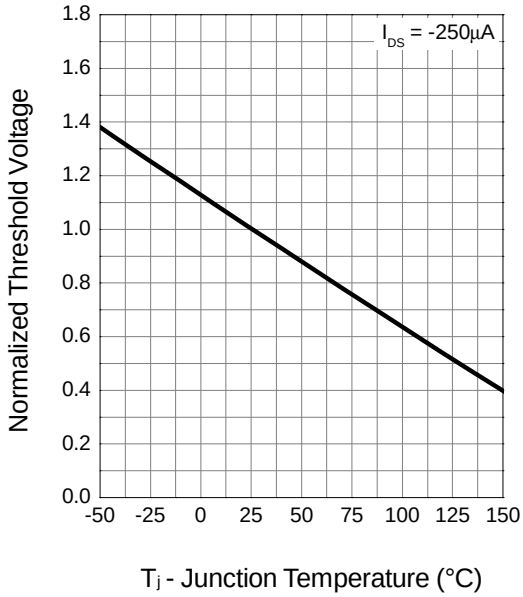
Drain-Source On Resistance



Transfer Characteristics



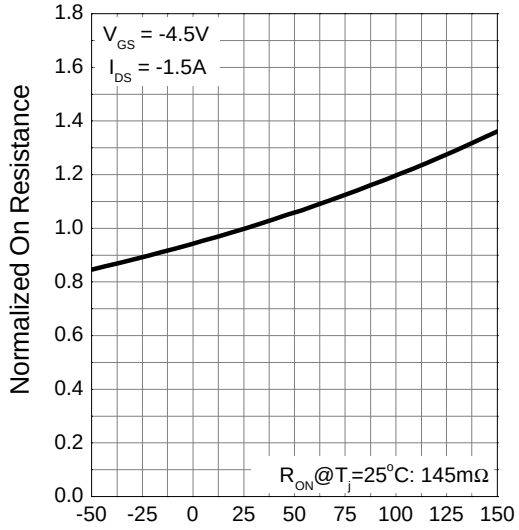
Gate Threshold Voltage



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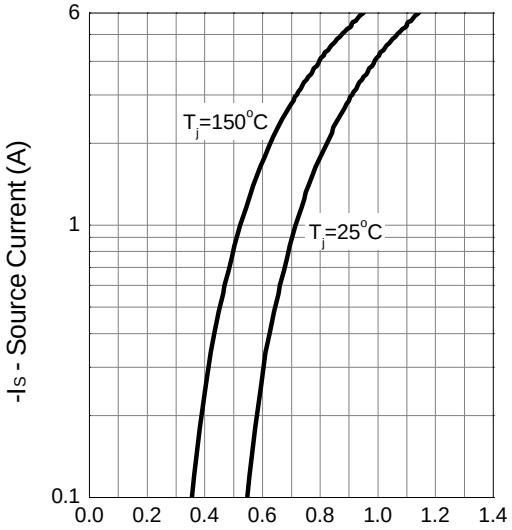
Typical Characteristics (Cont.)

Drain-Source On Resistance



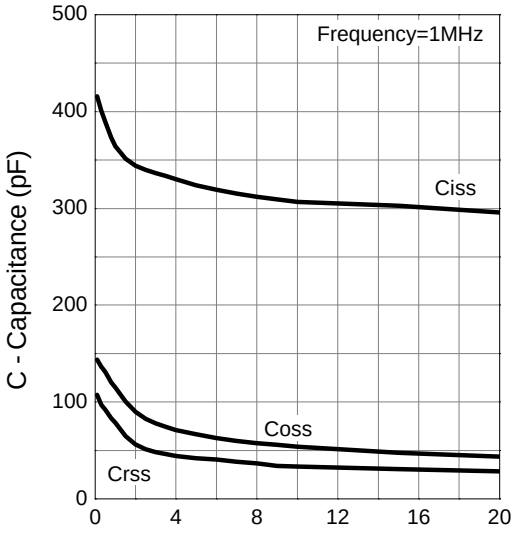
T_j - Junction Temperature (°C)

Source-Drain Diode Forward



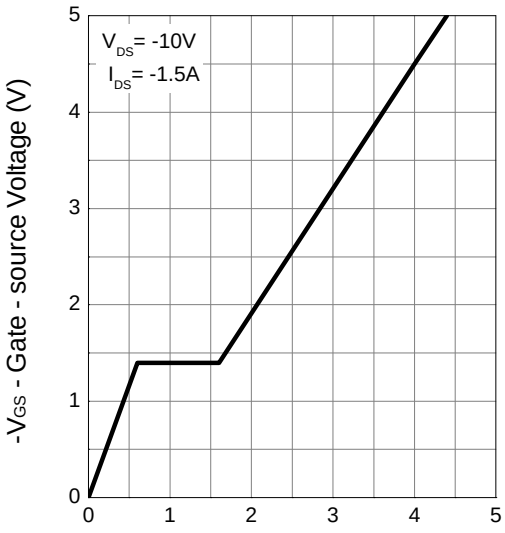
$-V_{SD}$ - Source - Drain Voltage (V)

Capacitance



$-V_{DS}$ - Drain - Source Voltage (V)

Gate Charge

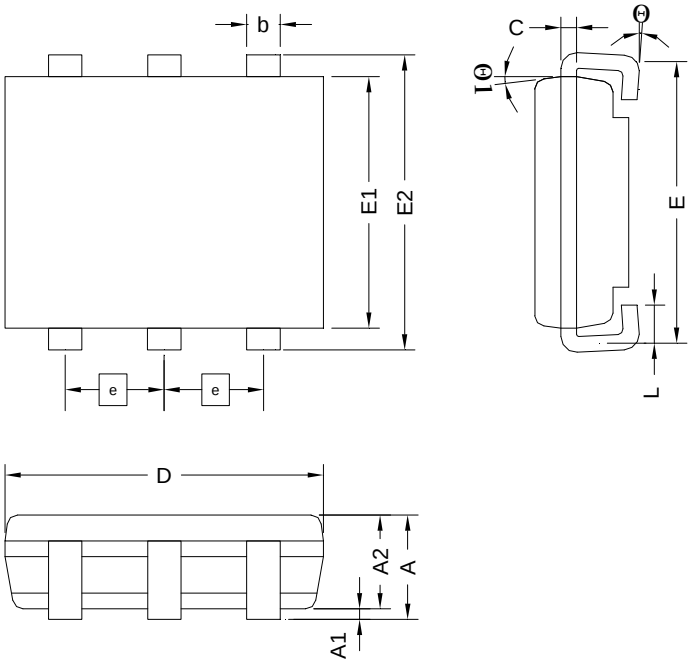


Q_G - Gate Charge (nC)

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Packaging Information

JSOT-6



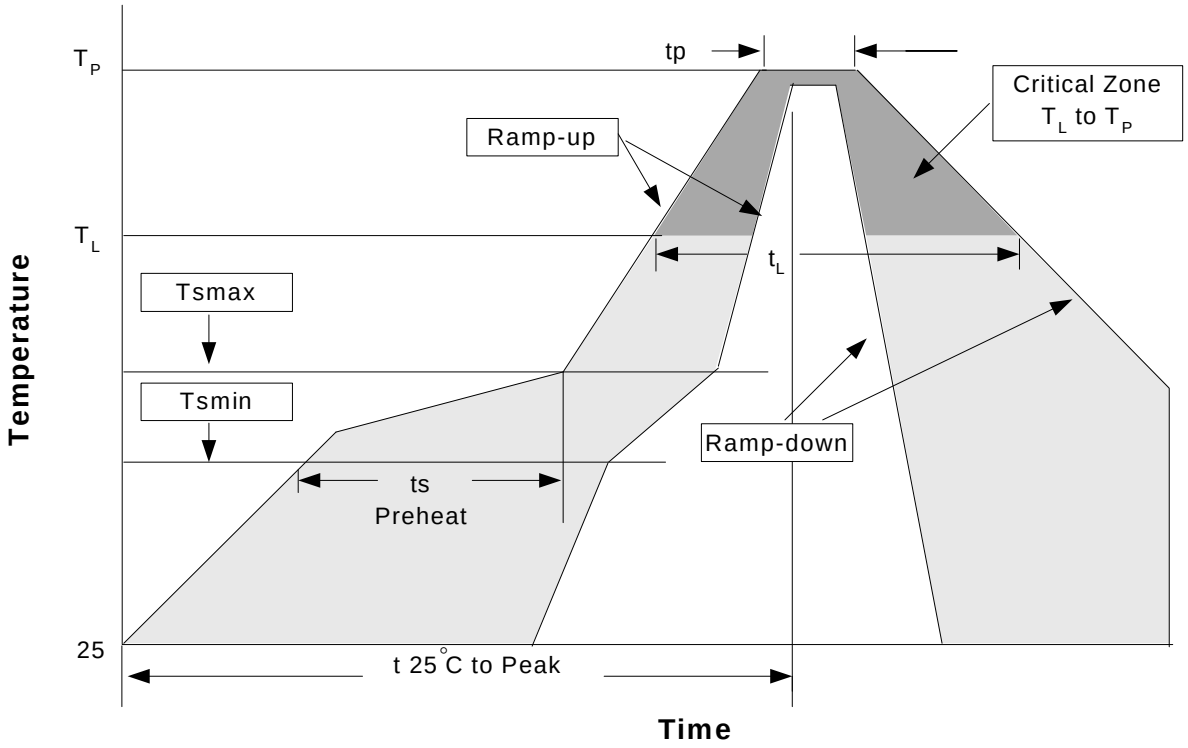
Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.935	1.10	0.037	0.043
A1	0.01	0.10	0.0004	0.004
A2	0.925	1.00	0.036	0.039
b	0.25	0.40	0.010	0.016
c	0.10	0.20	0.004	0.008
D	2.95	3.10	0.116	0.122
E	2.50	3.00	0.098	0.118
E1	2.30	2.50	0.091	0.098
E2	2.65	3.05	0.104	0.120
e	0.95 BSC		0.037 BSC	
L	0.30	0.60	0.012	0.024
?	0	8°	0	8°
?1	7° N0M.		7° N0M.	

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Physical Specifications

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb), 100%Sn
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.

Reflow Condition (IR/Convection or VPR Reflow)



Classificatin Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	3°C/second max.	3°C/second max.
Preheat - Temperature Min (Tsmin) - Temperature Max (Tsmax) - Time (min to max) (ts)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: - Temperature (T_L) - Time (t_L)	183°C 60-150 seconds	217°C 60-150 seconds
Peak/Classificatioon Temperature (Tp)	See table 1	See table 2
Time within 5°C of actual Peak Temperature (tp)	10-30 seconds	20-40 seconds
Ramp-down Rate	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Notes: All temperatures refer to topside of the package .Measured on the body surface.

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Classificatin Reflow Profiles(Cont.)

Table 1. SnPb Entectic Process – Package Peak Reflow Temperatures

Package Thickness	Volume mm^3 <350	Volume mm^3 ³350
<2.5 mm	240 +0/-5°C	225 +0/-5°C
≥2.5 mm	225 +0/-5°C	225 +0/-5°C

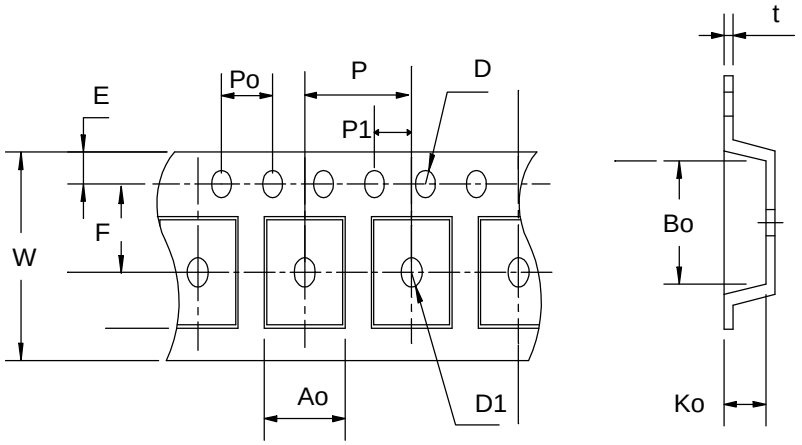
Table 2. Pb-free Process – Package Classification Reflow Temperatures

Package Thickness	Volume mm^3 <350	Volume mm^3 350-2000	Volume mm^3 >2000
<1.6 mm	260 +0°C*	260 +0°C*	260 +0°C*
1.6 mm – 2.5 mm	260 +0°C*	250 +0°C*	245 +0°C*
≥2.5 mm	250 +0°C*	245 +0°C*	245 +0°C*
*Tolerance: The device manufacturer/supplier **shall** assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0°C. For example 260°C+0°C) at the rated MSL level.			

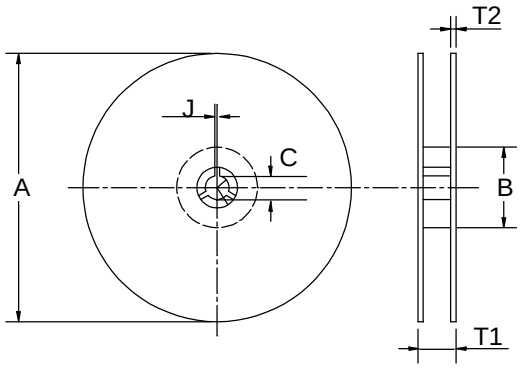
Reliability Test Program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C,5 SEC
HOLT	MIL-STD 883D-1005.7	1000 Hrs Bias @ 125°C
PCT	JESD-22-B, A102	168 Hrs, 100% RH, 121°C
TST	MIL-STD 883D-1011.9	-65°C ~ 150°C, 200 Cycles

Carrier Tape & Reel Dimensions



Carrier Tape & Reel Dimensions(Cont.)



Application	A	B	C	J	T1	T2	W	P	E
SOT-23-6	178±1	72 ± 1.0	13.0 + 0.2	2.5 ± 0.15	8.4 ± 2	1.5± 0.3	8.0+ 0.3 - 0.3	4 ± 0.1	1.75± 0.1
	F	D	D1	Po	P1	Ao	Bo	Ko	t
	3.5 ± 0.05	1.5 +0.1	1.5 +0.1	4.0 ± 0.1	2.0 ± 0.1	3.15 ± 0.1	3.2± 0.1	1.4± 0.1	0.2±0.03

(mm)

Cover Tape Dimensions

Application	Carrier Width	Cover Tape Width	Devices Per Reel
SOT-23-6	8	5.3	3000

Customer Service

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